NSN 5962-00-370-1132

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-00-370-1132

Body Length:

Between 0.660 inches and 0.785 inches

Body Width:

Between 0.220 inches and 0.280 inches

Body Height:

Between 0.140 inches and 0.180 inches

Maximum Power Dissipation Rating:

450.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Hermetically sealed and monolithic and positive outputs

Inclosure Material:

Ceramic and glass

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Current-mode logic

Input Circuit Pattern:

4 input

Case Outline Source And Designator:

T0-116 joint electron device engineering council

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

25.0 volts power source

Time Rating Per Chacteristic:

50.00 nanoseconds propagation delay time, low to high level output

Memory Device Type:

Diode matrix

Test Data Document:

07148-80771 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.;

excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

14 printed circuit

Shelf Life:

N/a

Unit Of Measure:

- ---
- Demilitarization:
- Yes demil/mli

NSN 5962-00-370-1132

Memory Microcircuit - Page 2 of 2

Fiig: A458a0

